

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-14. (canceled)

15. (previously presented) A method of manufacturing a semiconductor integrated circuit device having plural capacitor elements, the method comprising the steps of:

forming plural cylindrical crown structures of a first conducting material in a first insulating film on a substrate of the device, parts of the first insulating film being between bases of each of said plural cylindrical crown structures;

depositing a second conducting material on interior and exterior walls and an interior bottom of each of said cylindrical crown structures and on the first insulating material between said plural cylindrical crown structures, said second conducting material being more difficult to oxidize than said first conducting material, said second conducting material being thicker at tops of said cylindrical crown structures than at the interior bottoms thereof;

removing said second conducting material from said first insulating material between said plural cylindrical crown structures and in a same step decreasing a thickness of said second conducting material at the tops of said cylindrical crown

structures while retaining at least part of said second conducting material at the tops, on the interior and exterior walls, and on the interior bottom of each of said cylindrical crown structures;

following the removing step, growing a film of said second conducting material on the tops, interior and exterior walls and interior bottom of each of said cylindrical crown structures using the previously deposited said second conducting material as a seed for said film;

applying a second insulating film on the film of said second conducting material on the tops, the interior and exterior walls and the interior bottom of each of said cylindrical crown structures and on the first insulating material between said plural cylindrical crown structures; and

introducing oxygen into said second insulating film.